

**isc P-Channel MOSFET Transistor**

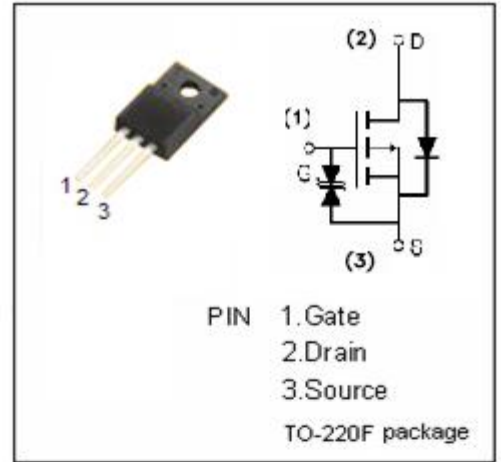
**2SJ376**

**DESCRIPTION**

- Low Drain-Source ON Resistance
- High Forward Transfer Admittance
- Low Leakage Current
- Enhancement-Mode

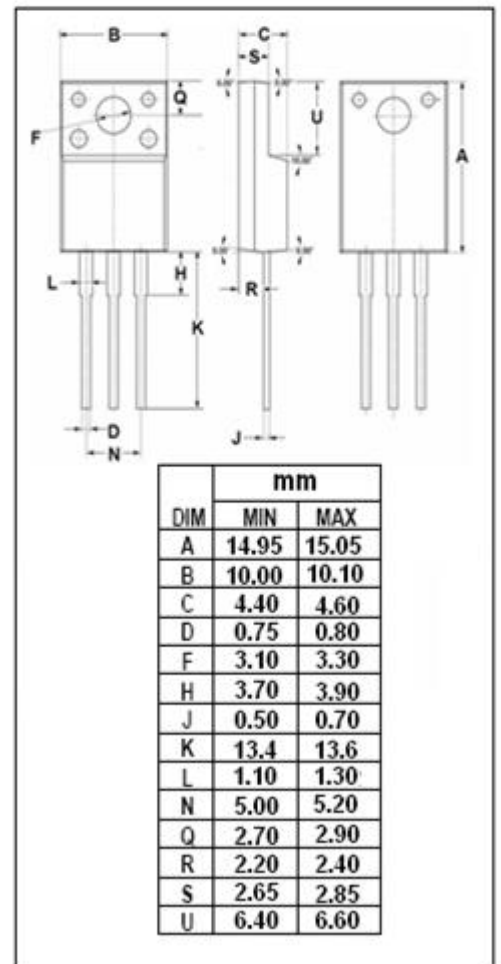
**APPLICATIONS**

- High speed switching application
- Switching regulator ,DC-DC converter and Motor drive application



**ABSOLUTE MAXIMUM RATINGS(T<sub>a</sub>=25°C)**

SYMBOL	ARAMETER	VALUE	UNIT
V <sub>DSS</sub>	Drain-Source Voltage (V <sub>GS</sub> =0)	-60	V
V <sub>GS</sub>	Gate-Source Voltage	±15	V
I <sub>D</sub>	Drain Current-continuous@ TC=37°C	-30	A
P <sub>tot</sub>	Total Dissipation@TC=25°C	50	W
T <sub>j</sub>	Max. Operating Junction Temperature	150	°C
T <sub>stg</sub>	Storage Temperature Range	-55~150	°C



**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	MAX	UNIT
R <sub>th j-c</sub>	Thermal Resistance,Junction to Case	3.1	°C/W
R <sub>th j-a</sub>	Thermal Resistance,Junction to Ambient	75	°C/W

**isc P-Channel Mosfet Transistor****2SJ376****• ELECTRICAL CHARACTERISTICS (T<sub>C</sub>=25°C)**

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
V <sub>(BR)DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> = 0; I <sub>D</sub> = -1mA	-60		V
V <sub>GS(TH)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> ; I <sub>D</sub> = -1mA	-1.0	-2.0	V
R <sub>DS(ON)</sub>	Drain-Source On-stage Resistance	V <sub>GS</sub> = -10V; I <sub>D</sub> = -15A		0.045	Ω
I <sub>GSS</sub>	Gate Source Leakage Current	V <sub>GS</sub> = -12V; V <sub>DS</sub> = 0		-10	uA
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = -60V, V <sub>GS</sub> = 0		-0.1	mA
V <sub>SD</sub>	Diode Forward Voltage	I <sub>F</sub> =-20A; V <sub>GS</sub> = 0		-1.5	V